

TSM19N20

200V N-Channel Power MOSFET



TO-252 (DPAK) **Pin Definition:**

- 1. Gate
- Drain
 Source



n ce

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
200	92 @ V _{GS} =10V	18

Features

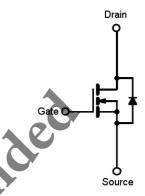
- Advanced Trench Technology
- Low $R_{DS(ON)}$ 92m Ω (Max.)
- Low gate charge typical @ 55nC (Typ.)
- Low Crss typical @ 73pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM19N20CP ROG	TO-252	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	200	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current @ T _C =25℃	I _D	18	А
Drain Current Pulsed (Note 1)	I _{DM}	72	А
Avalanche Current	I _{AS}	8	А
Avalanche Energy, L=10mH	E _{AS}	320	mJ
Maximum Power Dissipation @ T _C =25℃	P _D	48	W
Storage Temperature Range	T_{STG}	-55 to +150	S
Operating Junction Temperature Range	T_J	-55 to +150	C

^{*} Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Case	R⊖ _{JC}	2.6	°C/W	
Thermal Resistance - Junction to Ambient	R⊖ _{JA}	50	°C/W	

Notes: Surface mounted on FR4 board t ≤ 10sec

1/4 Version: A12



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	200			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 10A$	R _{DS(ON)}		80	92	mΩ
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	2		4	V
Zero Gate Voltage Drain Current	$V_{DS} = 160V, V_{GS} = 0V$	I _{DSS}			1	uA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge	$V_{DS} = 100V, I_D = 10A,$ $V_{GS} = 10V$	Q_g		55		nC
Gate-Source Charge		Q_{gs}		18		
Gate-Drain Charge		Q_{gd}	3	17		
Input Capacitance	$V_{DS} = 30V, V_{GS} = 0V,$	C _{iss}	9	2300		
Output Capacitance		Coss		145		pF
Reverse Transfer Capacitance	f = 1.0MHz	Crss		73		
Switching						
Turn-On Delay Time		t _{d(on)}		17		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 100V$	t _r		12		~ C
Turn-Off Delay Time	$R_G = 3\Omega$	$t_{d(off)}$		28		nS
Turn-Off Fall Time		t _f		10		
Drain-Source Diode Characteristics and Maximum Rating						
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =10A	V_{SD}			1.3	V
Reverse Recovery Time	I _S = 10A, T _J =25 °C	t _{fr}		82		nS
Reverse Recovery Charge	dl/dt = 100A/us	Q_fr		276		nC

2/4 Version: A12

Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
 Rθ_{JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Rθ_{JC} is guaranteed by design while Rθ_{CA} is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

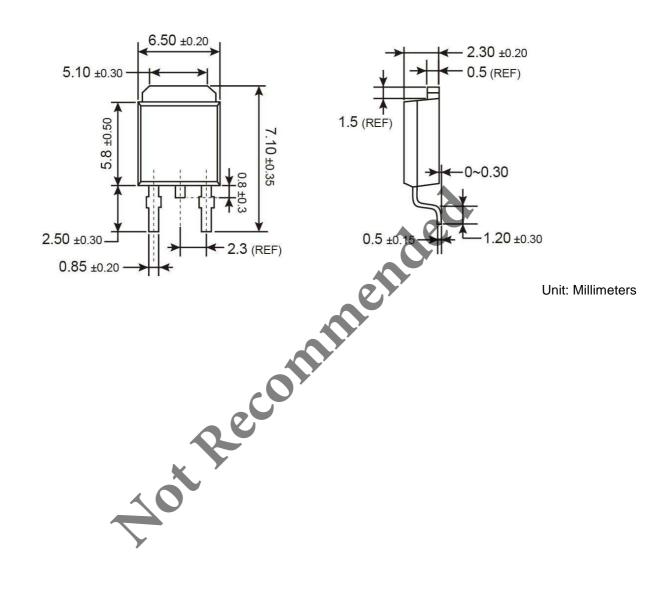


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TO-252 Mechanical Drawing



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